



GP
ELECTRONICS

GPM041ND03LND
30V Dual N-Channel MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)TYP}	I _D
30V	4.2mΩ@10V	60A
	5.5mΩ@4.5V	

Feature

- Trench Technology Power MOSFET
- Low R_{DS(ON)}
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

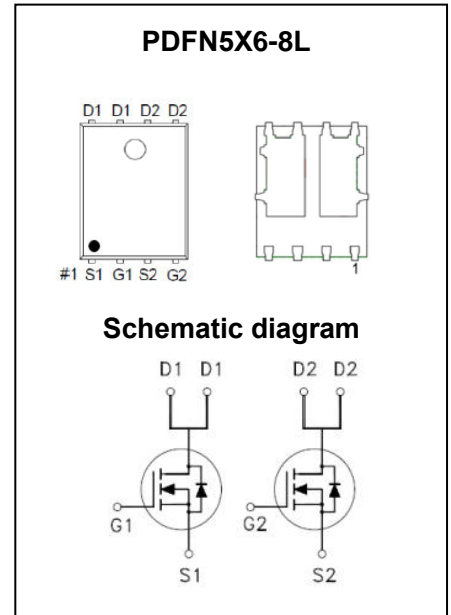
Application

- Power Switching Application

MARKING:



M041ND03L = Device Code
XX = Date Code
Solid Dot = Green Indicator



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V _{DS}	30	V
Gate - Source Voltage	V _{GS}	±20	V
Continuous Drain Current ¹	T _C = 25°C	I _D	60 A
	T _C = 100°C	I _D	37 A
Pulsed Drain Current ²	T _C = 25°C	I _{DM}	240 A
	T _C = 100°C	I _{DM}	115 A
Single Pulsed Avalanche Current ³	I _{AS}	30	A
Single Pulsed Avalanche Energy ³	E _{AS}	193	mJ
Power Dissipation ⁵	T _C = 25°C	P _D	44 W
Thermal Resistance from Junction to Ambient ⁶	T _A = 25°C	R _{θJA}	50 °C/W
Thermal Resistance from Junction to Case		R _{θJC}	2.8 °C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

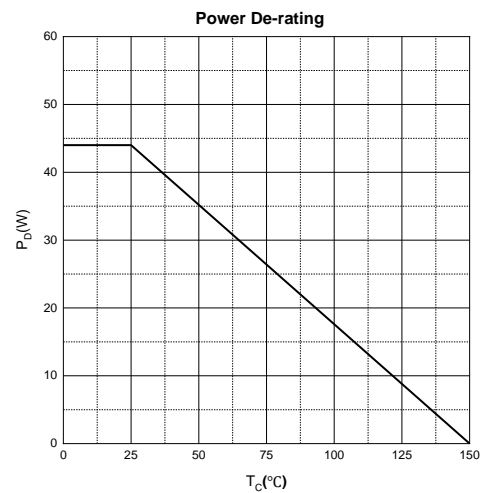
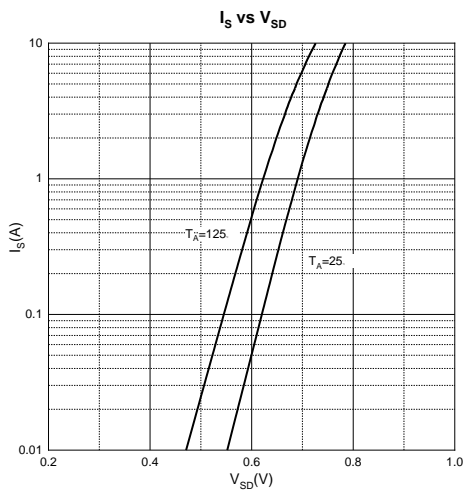
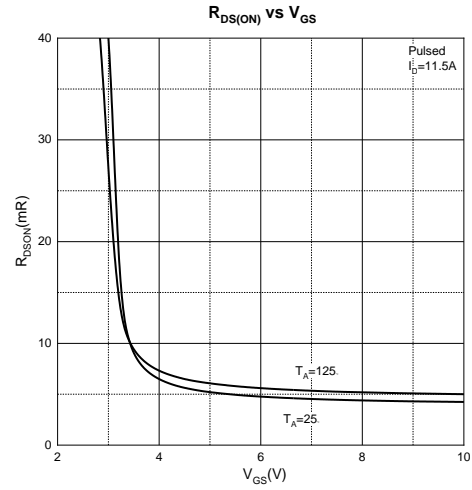
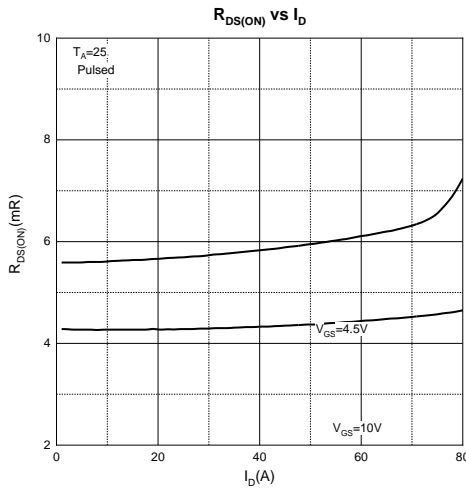
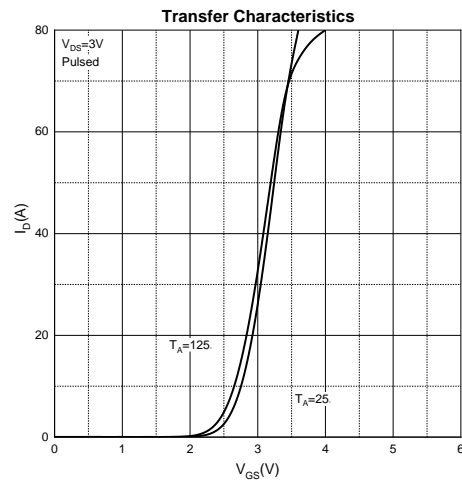
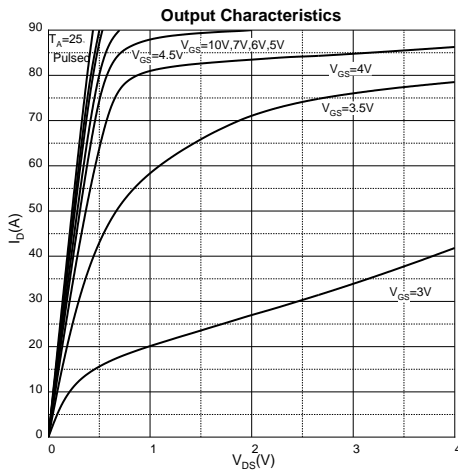
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

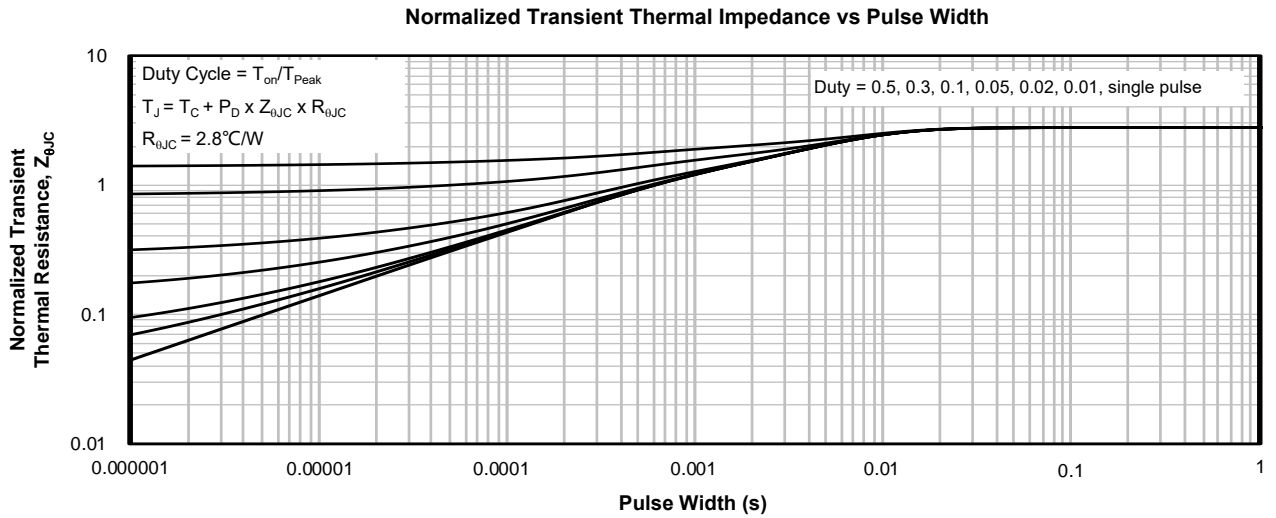
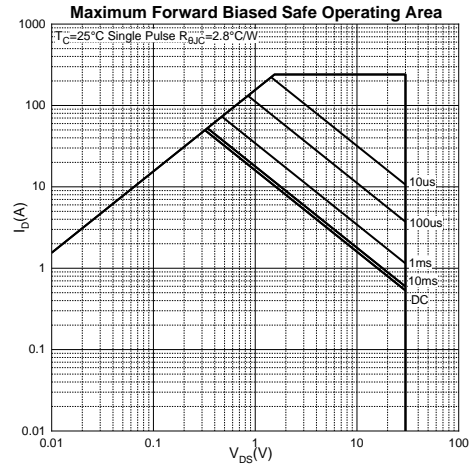
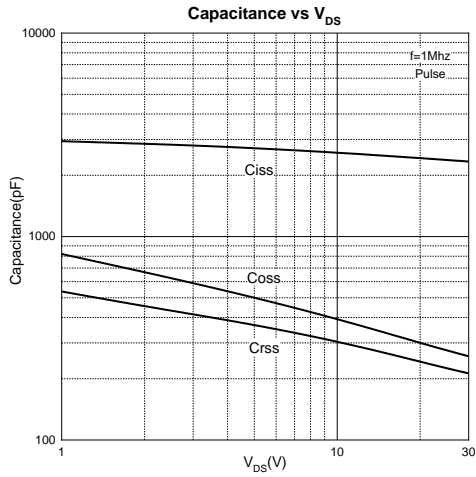
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.5	3.0	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		4.2	5.6	m Ω
		$V_{GS} = 4.5V, I_D = 15A$		5.5	7.5	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$		2587		pF
Output Capacitance	C_{oss}			357		
Reverse Transfer Capacitance	C_{rss}			284		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DD} = 15V, V_{GS} = 10V, I_D = 20A$		57.6		nC
Gate-source Charge	Q_{gs}			7.9		
Gate-drain Charge	Q_{gd}			14		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 15V, V_{GS} = 10V, I_D = 22.5A$ $R_G = 3\Omega$		10		ns
Turn-on Rise Time	t_r			65		
Turn-off Delay Time	$t_{d(off)}$			40		
Turn-off Fall Time	t_f			90		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 10A$			1.2	V

Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
3. E_{AS} condition: $V_{DD} = 15V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

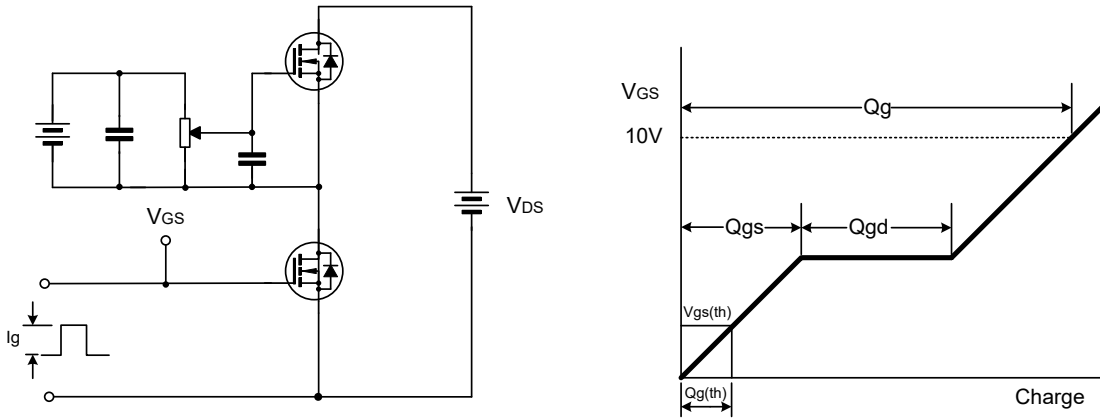
Typical Characteristics



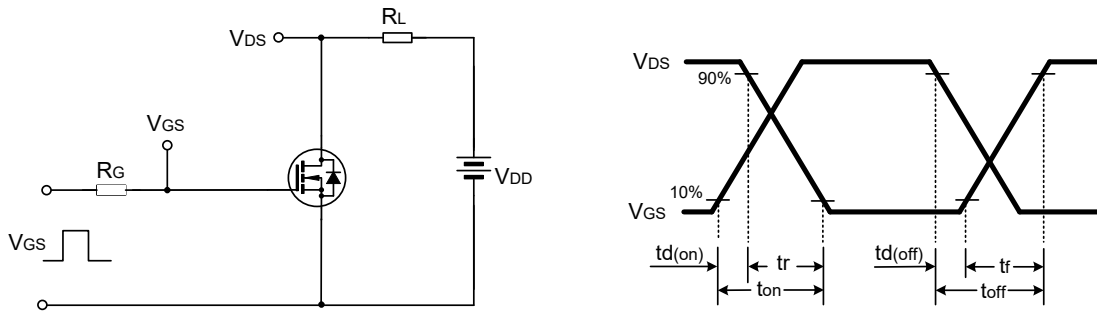


Test Circuit

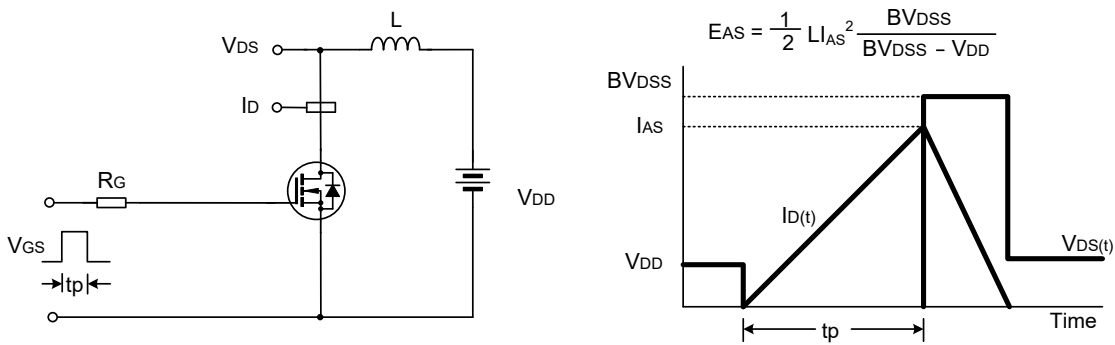
Gate Charge Test Circuit & Waveform



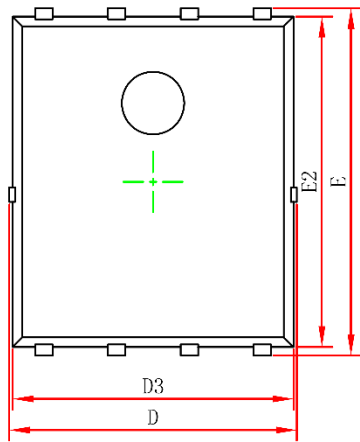
Resistive Switching Test Circuit & Waveform



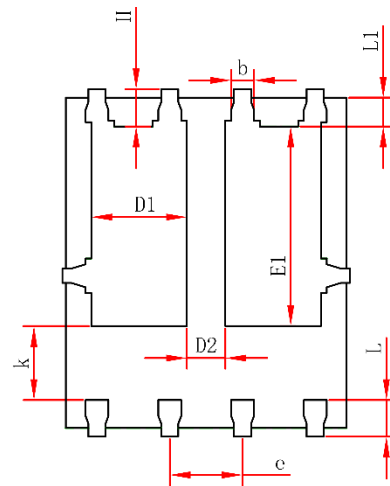
E_{AS} Test Circuit & Waveform



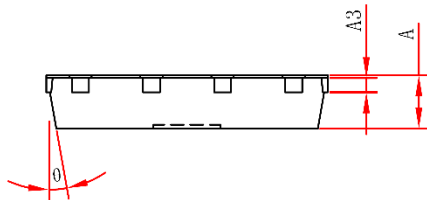
PDFN5X6-8L Package Information



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A3	0.210	0.340	0.008	0.013
D	4.900	5.100	0.193	0.201
E	5.900	6.100	0.232	0.240
D1	1.470	1.870	0.058	0.074
D2	0.470	0.870	0.019	0.034
E1	3.340	3.640	0.131	0.143
D3	4.800	5.000	0.189	0.197
E2	5.674	5.826	0.223	0.229
k	1.100	-	0.043	-
b	0.300	0.500	0.012	0.020
e	1.270TYB		0.050TYB	
L	0.510	0.710	0.020	0.028
L1	0.424	0.576	0.017	0.023
H	0.549	0.726	0.022	0.029
θ	8°	12°	8°	12°

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
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